	U	1	D	ocument	ID	Issue Date	Pages	Title	Current OR	Curre
1	П	R	US	6369490	В1	20020409	9	Surface acoustic wave device having bump electrodes	310/364	310/3
2	Б	Þ	US	5746930	Α	19980505	11	Method and structure for forming an array of thermal	216/87	216/10 216/5
3	П	Þ	US	5440125	A	19950808	5	Radiation detector having a pyroelectric ceramic	250/338.1	250/3: 501/1:
4	П	R	US	6064120	A	20000516	10	Apparatus and method for face-to-face connection of a	257/780	257/70 257/E
5	С	P	បទ	5985486	A	19991116	15	Electrochemical device	429/188	429/2: 429/3
6	П	Þ	US	5896081	A	19990420	11	Resistance temperature detector (RTD) formed with a	338/22R	
7	Г	P	បន	5777390	A	19980707	12	Transparent and opaque metal-semiconductor-metal	257/749	257/4 257/4
8	Г	M.		6137184		20001024	10	Flip-chip type semiconductor device having		257/73 257/73
9	П	M				19991130	11	Method of manufacture of surface acoustic wave device	29/25.35	310/3
10	Г		Í	6028011		20000222		Method of forming electric pad of semiconductor device	438/745	257/E2 438/6:
11			i				17	Surface acoustic wave devices having a guard layer	333/193	310/3 310/3
12	Г							Acoustic transducers utilizing ZnO thin film	310/334	310/36 310/36
13	Г					19920428		Method for forming a bump electrode for a		148/D1 257/69
14	П					19810331	4	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag	310/364	-
15	П	F	US	4736128	A	19880405	6	Surface acoustic wave device		310/31 310/34
16 •1	-	-	បទ	5325012	A	19940628	15	Bonded type piezoelectric	310/364	228/1

	U	1	D	ocument I	D	Issue Date	Pages	Title	Current OR	Current
11	ם	R	υs	5699027	A.	19971216	17	Surface acoustic wave devices having a guard layer	333/193	310/313 310/344
12	Г	M		4692653			10	Acoustic transducers utilizing ZnO thin film	310/334	310/364 310/365
13	Г	Þ	US	5108950 #	٩.	19920428	11	Method for forming a bump electrode for a	438/614	148/DIG 257/690
14	П	Ø	បទ	4259607 A	Α.	19810331	4	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag	310/364	
15	Г	P	US	4736128 A	٩.	19880405	6	Surface acoustic wave device	310/313R	310/313 310/348
16	П	P	US	5325012 A	١.	19940628	15	Bonded type piezoelectric apparatus, method for	310/364	228/121 228/124
17	г	Þ	US	6277523 E	31	20010821	14	Electrochemical device	429/304	429/33
18	Г	M	ĺ	07187894	:		4	Ferroelectric thin film for substrate material for	and the state of the state that and the state of the state	
19	Г	Ø	US	5134460 A	`	19920728	10	Aluminum bump, reworkable bump, and titanium nitride	257/737	257/733 257/771
20	г	Þ	JP	54128280	A	19791004		RESIN-SEALED SEMICONDUCTOR DEVICE		257/766 257/771
21	П	M	(	4330182 A	:		11	Method of forming semiconducting materials and	257/56	136/249 136/258
22	П	F	US	5591321 A	`	19970107	•	Detection of fluids with metal-insulator-semiconducto	205/787	204/401 204/412
23	г	<b>P</b>		6404110 E			7	Surface acoustic wave element having a bump	310/364	310/313
24	П	14.		6326052 E			8	get to the to get to get the contract of the contract to get the contract to get the contract to get the get the get the get to get the get to get the get to get the get to get the g	427/79	204/192 29/25.4
25	П	F	JР	60116168	A	19850622	-	WIRING ELECTRODE OF EQUAL MAGNIFICATION SENSOR		257/459 257/E31